

## Features

- 200 Watts Peak Pulse Power per Line ( $t_p = 8/20\mu s$ )
- Protects one I/O or power line
- Low Clamping Voltage
- Working Voltage: 12V
- Low Leakage Current

**SOD-523**

## IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 30kV$  (air),  $\pm 30kV$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 8A (8/20 $\mu s$ )

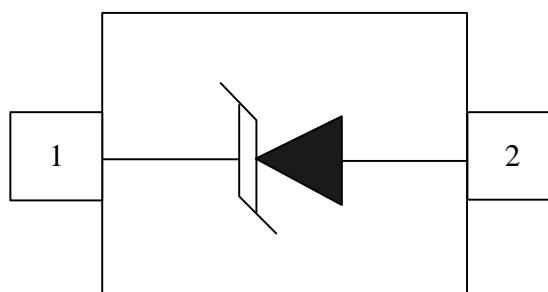
## Mechanical Characteristics

- JEDEC SOD-523 package
- Marking : Marking Code
- Packaging : Tape and Reel per EIA 481
- RoHS Compliant

## Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras
- MP3 players

## Schematic & PIN Configuration



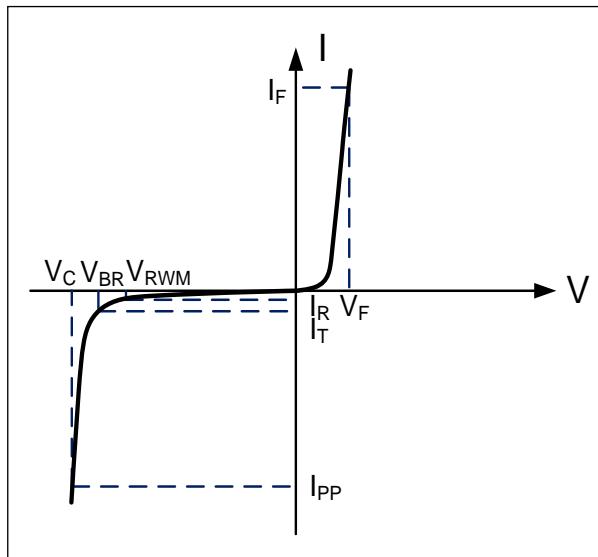
SOD-523 (Top View)

### Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p=8/20\mu s$ )	$P_{PP}$	200	W
Peak Pulse Current ( $t_p=8/20\mu s$ )	$I_{PP}$	8	A
Operating Temperature	$T_J$	-55 to + 125	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C

### Electrical Parameters (T=25°C)

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



### Electrical Characteristics

CES5Z12V						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				12	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1\text{mA}$	13.3			V
Forward Voltage	$V_F$	$I_T=10\text{mA}$	0.5		1.0	V
Reverse Leakage Current	$I_R$	$V_{RWM}=12\text{V}, T=25^\circ\text{C}$			500	nA
Clamping Voltage	$V_C$	$I_{PP}=8\text{A}, t_p=8/20\mu\text{s}$		21	30	V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	$\text{TLP}=0.2/100\text{ns}$		0.22		Ω
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 4\text{A}, t_p = 0.2/100\text{ns} (\text{TLP})$		15.3		V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 16\text{A}, t_p = 0.2/100\text{ns} (\text{TLP})$		17.9		V
Junction Capacitance	$C_j$	$V_R = 0\text{V}, f = 1\text{MHz}$		40	55	pF

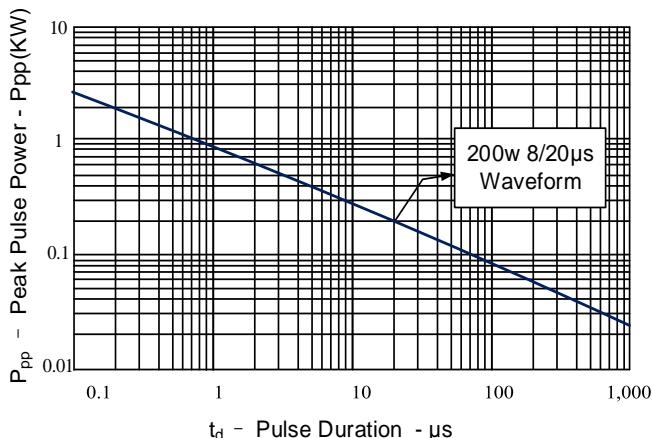
Notes : 1、TLP Setting :  $t_p=100\text{ns}$ ,  $t_r=0.2\text{ns}$ ,  $I_{TLP}$  and  $V_{TLP}$  sample window: $t_1=70\text{ns}$  to  $t_2=90\text{ns}$ .

2、Dynamic resistance calculated from  $I_{PP}=4\text{A}$  to  $I_{PP}=16\text{A}$  using "Best Fit".

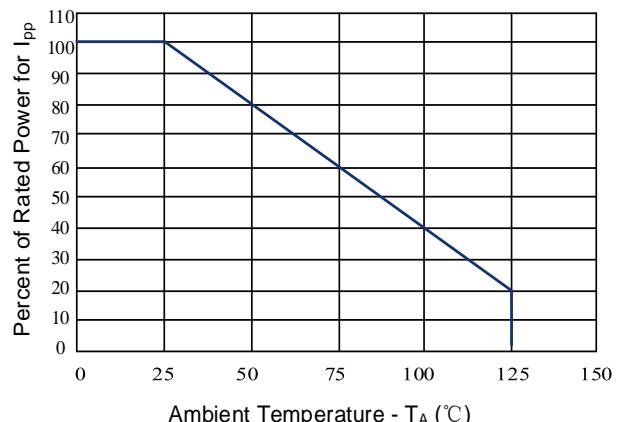
Ver.1.0

## Typical Characteristics

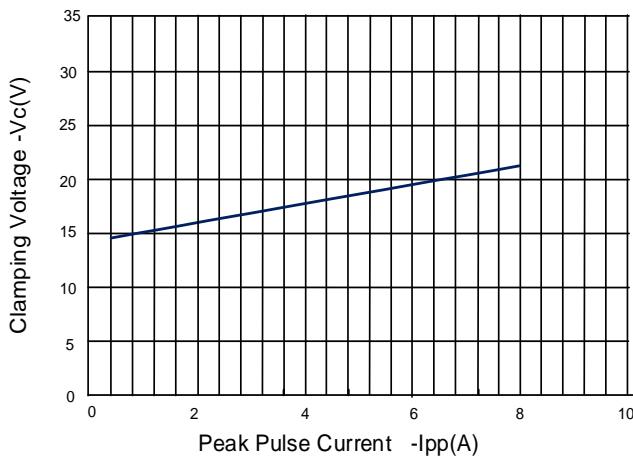
**Figure 1: Peak Pulse Power vs. Pulse Time**



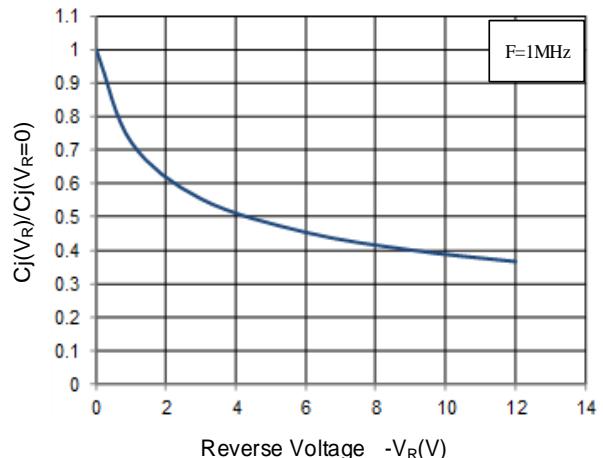
**Figure 2: Power Derating Curve**



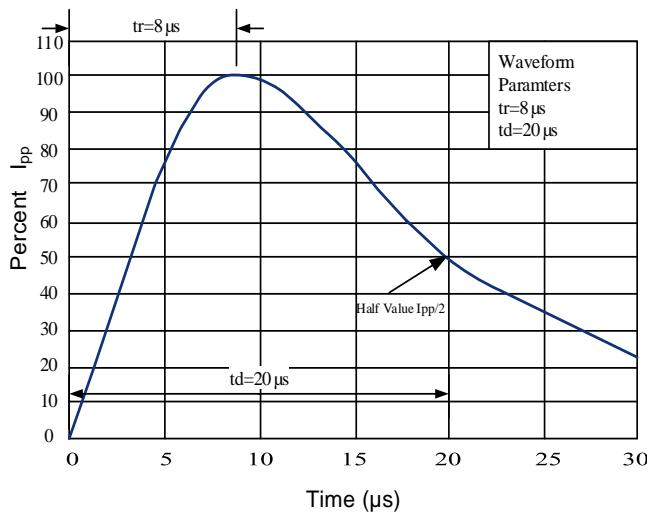
**Figure 3: Clamping Voltage vs. Peak Pulse Current**



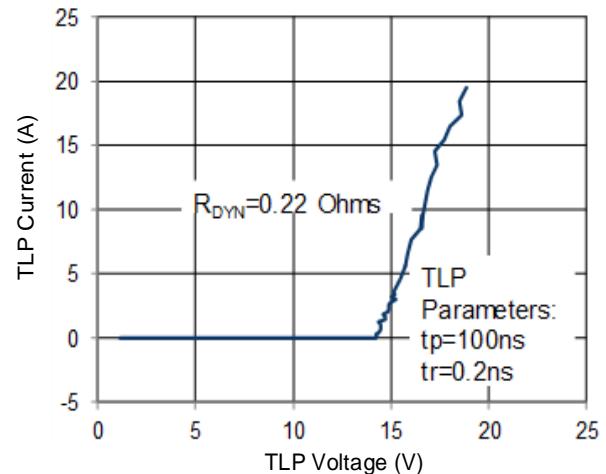
**Figure 4: Normalized Junction Capacitance vs. Reverse Voltage**



**Figure 5: Pulse Waveform**

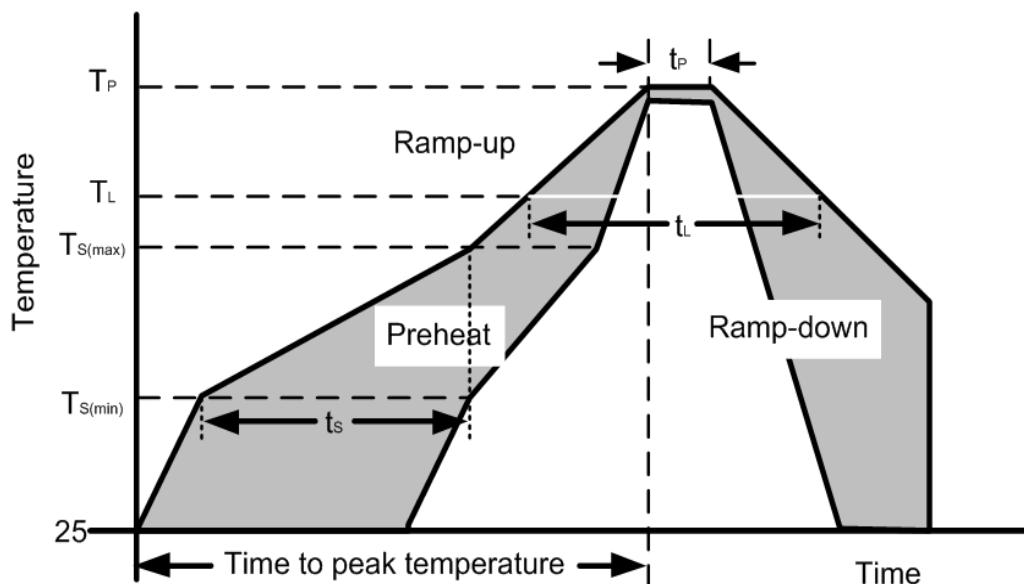


**Figure 6: TLP I-V Curve**



## Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{s(min)}$ )	150°C
	Temperature Max ( $T_{s(max)}$ )	200°C
	Time (min to max) (ts )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{S(max)}$ to $T_L$ —Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
	Peak Temperature ( $T_P$ )	260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C



## Outline Drawing –SOD-523

PACKAGE OUTLINE		DIMENSIONS			
SYMBOL	MILLIMETERS	INCHES			
	MIN	MAX	MIN	MAX	
A	0.50	0.70	0.020	0.028	
A1	0.00	0.07	0.000	0.003	
b	0.25	0.35	0.010	0.014	
C	0.07	0.20	0.003	0.008	
D	1.10	1.30	0.043	0.051	
E	0.70	0.90	0.028	0.035	
H <sub>E</sub>	1.50	1.70	0.059	0.067	
L	0.15	0.25	0.006	0.010	

DIMENSIONS: MILLIMETERS

**Notes:**  
Controlling Dimension: Millimeter.